

1. PRODUCT Super Fast Recovery Diode (Silicon Epitaxial Planer)
2. TYPE RF601BM2D
3. APPLICATION General rectification
4. FEATURE
 - Cathode common dual type
 - Low switching loss
 - Low forward voltage

5. ABSOLUTE MAXIMUM RATING (at Tc=25°C unless otherwise specified)

Item	Symbol	Conditions	Ratings	Unit
Repetitive peak reverse voltage	VRM	Duty ≤ 0.5	200	V
Reverse voltage	VR	Direct reverse voltage	200	V
Average current	Io	60Hz half sin wave, resistive load at Tc=109°C, 1/2Io per diode	6	A
Non-repetitive forward surge current	IFSM	60Hz half sin wave, one cycle, non-repetitive at Tj=25°C, per diode	60	A
Operating junction temperature	Tj		150	°C
Storage temperature	Tstg		-55~150	°C

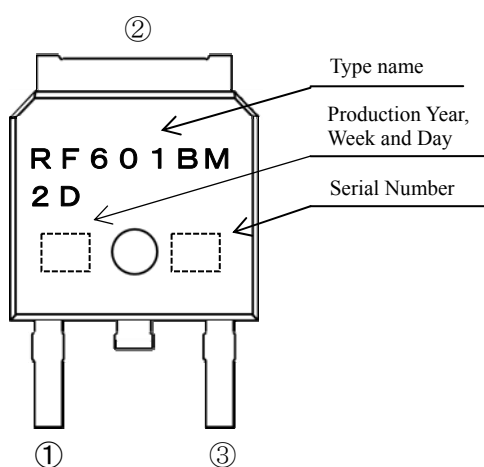
6. ELECTRICAL CHARACTERISTICS (at Tj=25°C unless otherwise specified, per diode)

Characteristic	Symbol	Test Condition	Specification			Unit
			Min.	Typ.	Max.	
Forward voltage	VF	IF=3A	—	0.87	0.93	V
Reverse current	IR	VR=200V	—	0.05	10	μA
Reverse recovery time ^(*)	trr	IF=0.5A, IR=1A, Irr=0.25×IR	—	14	25	ns
Thermal resistance ^(*)	Rth(j-c)	Junction to case	—	—	6.0	°C/W

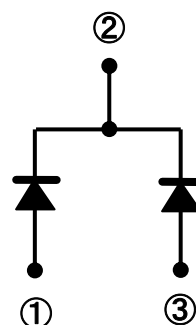
(*) : Design assurance without measurement

7. MARKING AND CONNECTION

Marking

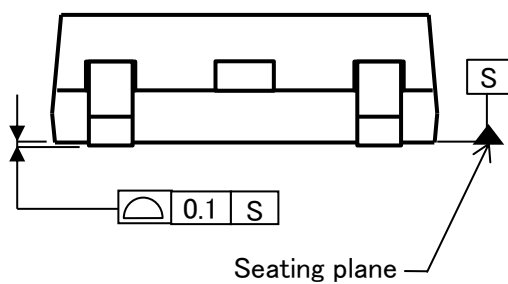
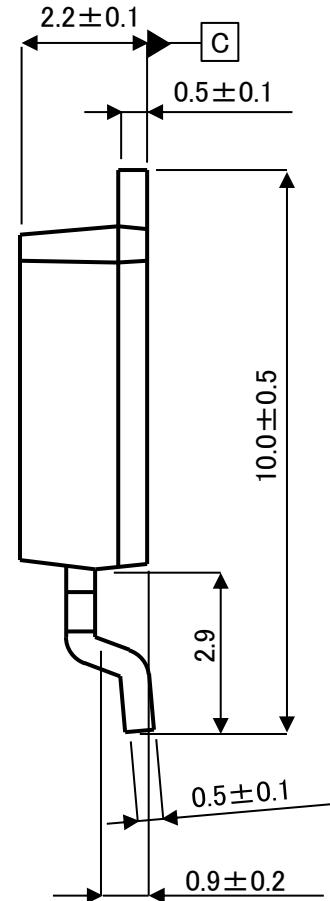
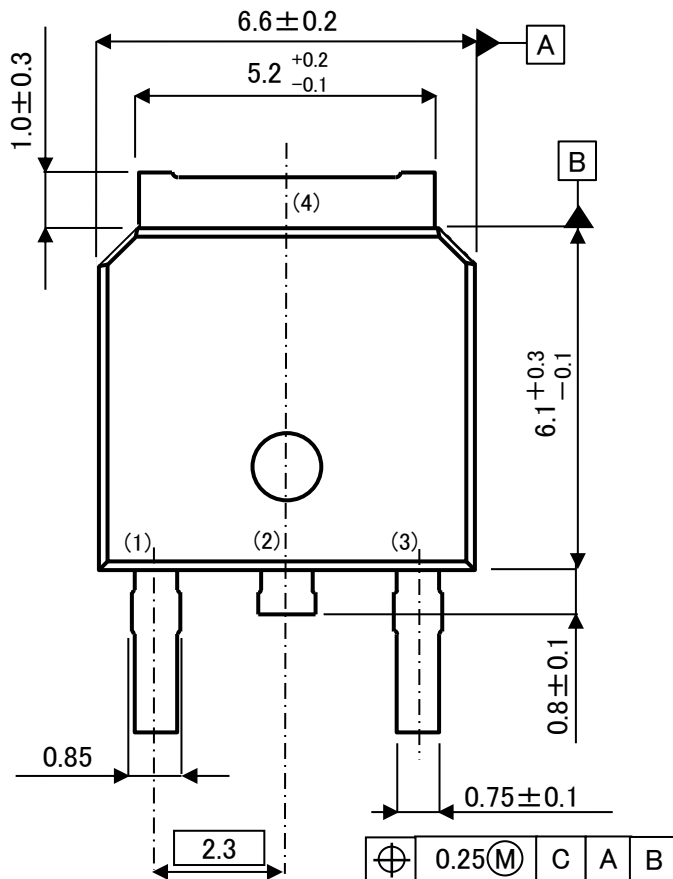


Connection



DESIGN <i>R. Nakagawa</i>	CHECK	APPROVAL <i>T. Koshino</i>	DATE:13.AUG.2013	SPECIFICATION No. : RF601BM2D-E
			REV. : A	ROHM Co.,Ltd.

1. OUTLINE DIMENSION
Marking side



UNIT : mm

DESIGN

H. Saito

CHECK

APPROVAL

Y. Matsuka

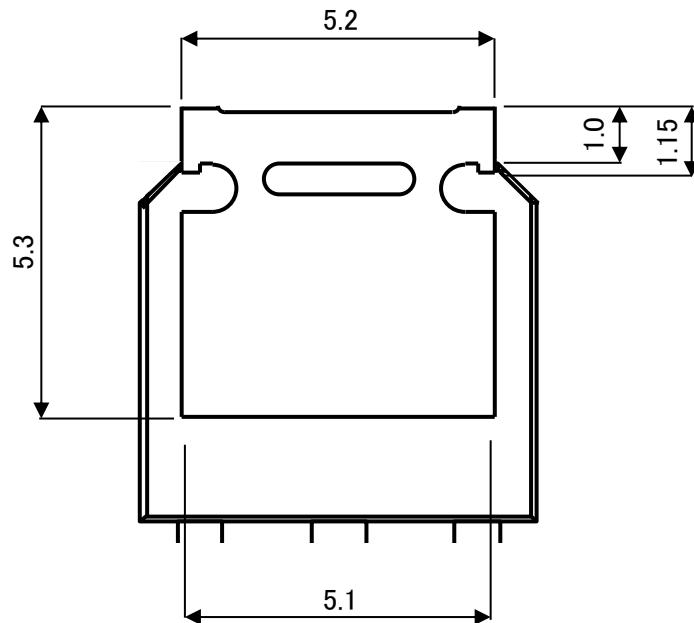
DATE: 10.AUG.2012

SPECIFICATION No.: TZ-TO252

REV. A

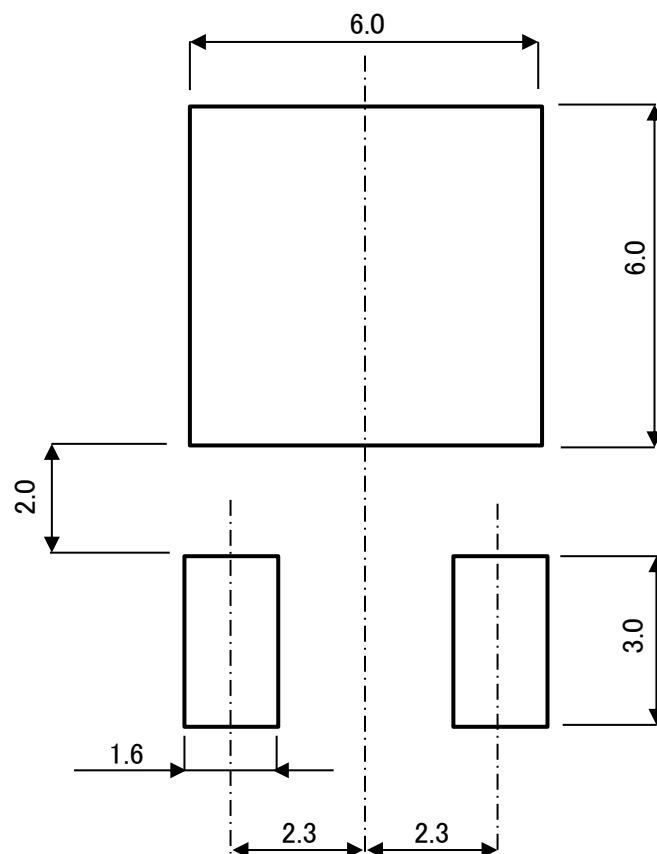
ROHM Co., Ltd.

Back side
(Reference)



UNIT : mm

2. RECOMMENDED PAD DIMENSION



UNIT : mm